United States Patent

Rairden, III

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[54] **RESISTOR THIN FILMS FORMED BY LOW-PRESSURE DEPOSITION OF MOLYBDENUM AND TUNGSTEN**

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[73] Assignee: **General Electric Company**

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[52] **U.S. Cl.** **117/227,** 117/107, 204/192, 338/308

[51] **Int. Cl.** **H01c 7/00**

[58] **Field of Search** .....117/227, 106 C, 107; 204/192; 338/308

[56] **References Cited**

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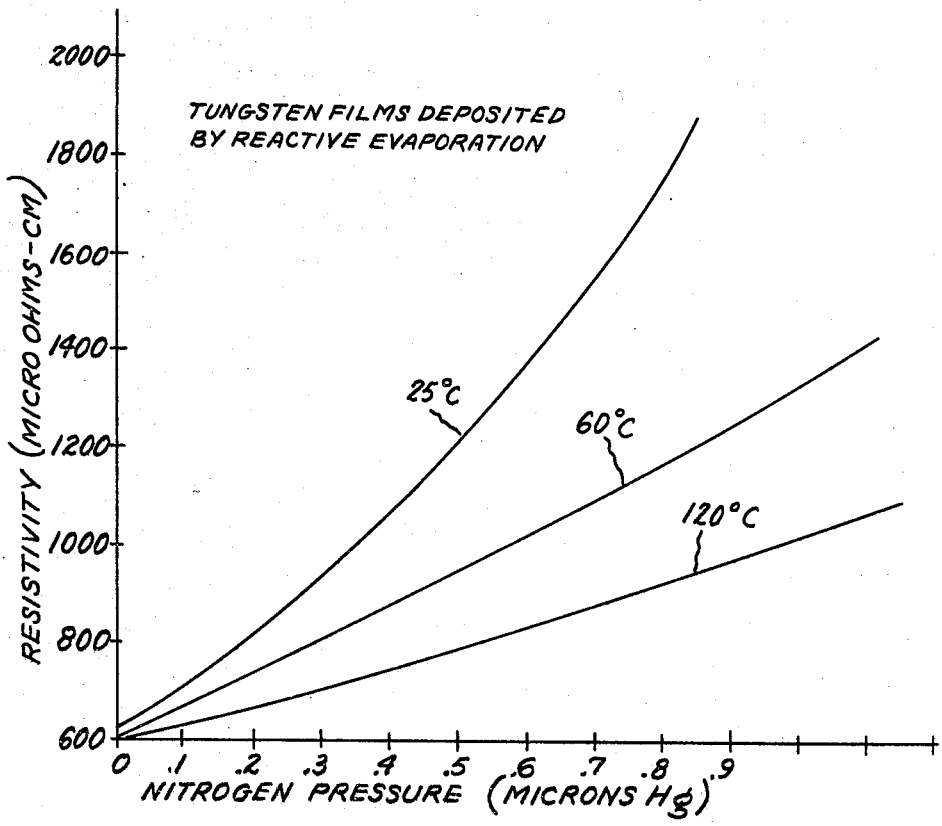
[57] **ABSTRACT**

High resistivity, low temperature coefficient of resistance films are formed by evaporating a molybdenum or tungsten source in a low-pressure atmosphere, e.g. 5×10^{-4} torr, of a nitrogen bearing gas, a carbon bearing gas or an inert gas and depositing a resistor film atop a preferably unheated dielectric substrate.

12 Claims, 8 Drawing Figures